L Number	Hits	Search Text	DB	Time stamp
1	2811689	memory or storage	USPAT;	2004/04/15 11:38
			US-PGPUB;	
			EPO; JPO;	
	_		DERWENT	
2	14611	(memory or storage) and cell with transistor with capacitor	USPAT;	2004/04/15 11:39
			US-PGPUB;	
			EPO; JPO;	
	620	//	DERWENT	2004/04/45 44 40
3	628	((memory or storage) and cell with transistor with capacitor)	USPAT;	2004/04/15 11:40
		and refresh\$5 with transistor with cell	US-PGPUB;	
			EPO; JPO; DERWENT	
4	313	((memory or storage) and cell with transistor with capacitor)	USPAT;	2004/04/15 11:40
'		and normal with transistor with cell	US-PGPUB;	2004/01/13 11.10
		and normal man dansiocol man con	EPO; JPO;	
			DERWENT	
5	24	(((memory or storage) and cell with transistor with	USPAT;	2004/04/15 11:41
		capacitor) and normal with transistor with cell) and	US-PGPUB;	
		refresh\$5 near3 amplifier	EPO; JPO;	
			DERWENT	

L Number	Hits	Search Text	DB	Time stamp
1	2811689	memory or storage	USPAT;	2004/04/15 14:01
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
2	14611	(memory or storage) and cell with transistor with capacitor	USPAT;	2004/04/15 14:03
			US-PGPUB;	
			EPO; JPO;	
	620		DERWENT	
3	628	((memory or storage) and cell with transistor with capacitor)	USPAT;	2004/04/15 14:04
		and refresh\$5 with transistor with cell	US-PGPUB;	
			EPO; JPO;	
4	57	(((memory or storage) and cell with transistor with	DERWENT USPAT:	2004/04/15 14:05
'	37	capacitor) and refresh\$5 with transistor with cell) and	US-PGPUB;	2004/04/15 14:05
		normal with transistor with cell	EPO; JPO;	
		· ·	DERWENT	
5	18	((((memory or storage) and cell with transistor with	USPAT;	2004/04/15 14:05
		capacitor) and refresh\$5 with transistor with cell) and	US-PGPUB;	200 ., 0 ., 10 11.00
		normal with transistor with cell) and refresh\$5 near3	EPO; JPO;	
		amplifier	DERWENT	

L Number	Hits	Search Text	DB	Time stamp
1	2811689	memory or storage	USPAT;	2004/04/15 15:27
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
2	14611	(memory or storage) and cell with transistor with capacitor	USPAT;	2004/04/15 15:30
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
3	400	((memory or storage) and cell with transistor with capacitor)	USPAT;	2004/04/15 15:38
	ļ	and chang\$5 with (potential or voltage or level) with plate	US-PGPUB;	
			EPO; JPO;	
			DERWENT	2004/04/45 45 24
4	2	(((memory or storage) and cell with transistor with	USPAT;	2004/04/15 15:34
		capacitor) and chang\$5 with (potential or voltage or level)	US-PGPUB;	
		with plate) and belt with plate	EPO; JPO; DERWENT	
-	4	(((momony or storage) and cell with transister with	USPAT;	2004/04/15 15:36
5	"	(((memory or storage) and cell with transistor with capacitor) and chang\$5 with (potential or voltage or level)	US-PGPUB;	2004/04/13 13.30
		with plate) and (correct\$5 or compensat\$5) with (voltage or	EPO; JPO;	
		potential or level) with leak\$5 with capacitor	DERWENT	
6	189	((memory or storage) and cell with transistor with capacitor)	USPAT;	2004/04/15 15:39
"	105	and chang\$5 with (potential or voltage or level) with plate	US-PGPUB;	2001/01/15 15:05
		with capacitor	EPO; JPO;	
		Tital supersise.	DERWENT	
7	20	((memory or storage) and cell with transistor with capacitor)	USPAT;	2004/04/15 15:40
		and chang\$5 with (potential or voltage or level) with plate	US-PGPUB;	, ,
		with capacitor with current	EPO; JPO;	
	1	·	DERWENT	